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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)		Complete if Known	
		Application Number	10/786,354
		Filing Date	February 25, 2004
		First Named Inventor	Ahn, Kie
		Group Art Unit	2818
		Examiner Name	Huynh, Andy
Sheet 1 of 1		Attorney Docket No: 303.686US3	

## US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
Ah	US-20010002333	05/31/2001	Huang, Chao-Yuan , et al.	438	637	03/29/1999
	US-1,254,987	01/29/1918	Cooper, H. S.			10/15/1917
	US-1,976,375	10/09/1934	Smith, J. K.	148	11.5	01/27/1931
	US20020109233	08/15/2002	Farrar, Paul A.	257	762	04/05/2002
	US-2,244,608	06/03/1941	Cooper, H. S.	75	138	02/09/1939
	US-2,842,438	07/08/1958	Saarivirta, M. J., et al.	75	153	08/02/1956
	US-3,147,110	09/01/1964	Foerster, G. S.	75	122.5	11/27/1961
	US-3,506,438	04/14/1970	Krock, R. H., et al.	75	208	07/24/1967
	US-3,548,948	12/22/1970	Richmond, W. J., et al.	164	68	01/23/1969
	US-3,687,737	08/29/1972	Krock, R. H., et al.	148	2	07/17/1970
	US-3,923,500	12/02/1975	Kitazawa, Kunio , et al.	75	156.5	09/04/1974
	US-4,213,818	07/22/1980	Lemons, Kyle E., et al.	438	719	01/04/1979
	US-5,668,398	09/16/1997	Havemann, R. H., et al.	257	522	04/12/1996
	US-6,197,181	03/06/2001	Chen, Linlin	205	123	03/20/1998
	US-6,268,277	07/31/2001	Bang, D	438	619	07/16/1999
Ah	US-6,448,331	09/10/2002	Ioka, T. , et al.	524	859	11/12/1999

## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
Ah	EP-0304046	02/22/1989	Fujimura, S. , et al.	G03F	7/26	
	JP-05267643	10/15/1993	Muraoka, Toru	029	46	
	JP-07-321111	08/12/1995	Tetsuo, K.	H01L	21/3205	
Ah	JP-07078815	03/20/1995	Miyamoto, I.	H01L	21/3205	

## OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
Ah		"Brooks Model 5964 High Performance Metal Seal Mass Flow Controller (Introduced in 1991)", Brooks Instrument, <a href="http://www.frco.com/brooks/semiconductor/products1i.html">http://www.frco.com/brooks/semiconductor/products1i.html</a> , (1991), 1 page	

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Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)	<i>Complete if Known</i>	
	Application Number	Unknown 10/786,354
	Filing Date	Even Date Herewith
	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 1 of 13		Attorney Docket No: 303.686US3

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
Ah	US20010054771	12/27/2001	Wark, J. M., et al.			
	US20020014646	02/07/2002	Tsu, , et al.	257	296	
	US20020028552	03/07/2002	Lee, , et al.	438	243	
	US20020096768	07/25/2002	Joshi, Rajiv Vasant	257	750	
	US-3,337,334	08/22/1967	Fenn, R. W., et al.	75	150	12/06/1963
	US-3,548,915	10/22/1970	Richmond, W. J., et al.	164	68	06/11/1969
	US-3,832,456	08/27/1974	Kobetz, Paul , et al.	423	645	10/18/1962
	US-3,923,500	12/02/1975	Kitazawa, Kunio , et al.	75	156.5	09/04/1974
	US-3,932,226	01/13/1976	Klatskin, J. B., et al.	204	16	12/06/1974
	US-3,954,570	06/04/1976	Shirk, Albert , et al.	204	15	11/11/1974
	US-4,022,931	05/10/1977	Black, J. , et al.	427	91	06/13/1975
	US-4,029,377	06/14/1977	Guglielmi, A. C.	339	19	02/03/1976
	US-4,065,330	12/27/1977	Masumoto, Hakaru , et al.	148	31.55	02/22/1977
	US-4,101,855	07/18/1978	Drapeau, Donald R.	335	106	11/05/1976
	US-4,158,719	06/19/1979	Frantz, E.	428	567	06/09/1977
	US-4,233,066	11/11/1980	Sundin, Anders O., et al.	75	142	08/14/1975
	US-4,314,594	02/09/1982	Pfeifer, Friedrich , et al.	148	108	04/29/1980
	US-4,386,116	05/31/1983	Nair, Krishna K., et al.	427	99	12/24/1981
	US-4,389,429	06/21/1983	Soclof, Sidney I.	438	492	06/28/1982
	US-4,394,223	07/19/1983	Hall, Dean	204	15	10/06/1981
	US-4,423,547	01/03/1984	Farrar, P. A., et al.	29	571	06/01/1981
	US-4,561,173	12/31/1985	Te Velde, T. S.	438	619	06/07/1983
	US-4,565,157	01/21/1986	Brors, D. L., et al.	118	719	03/29/1983
	US-4,574,095	03/04/1986	Baum, Thomas H., et al.	427	53.1	11/19/1984
	US-4,670,297	06/02/1987	Lee, K. , et al.	427	91	06/21/1985
US-4,709,359	11/24/1987	Loftin, Rayford A.	367	155	06/28/1982	
US-4,762,728	08/09/1988	Keyser, T. , et al.	427	38	11/26/1985	
US-4,788,082	11/29/1988	Schmitt, Jerome J.	427	248.1	12/12/1985	
US-4,847,111	07/11/1989	Chow, Yu C., et al.	427	38	06/30/1988	
US-4,857,481	08/15/1989	Tam, G. , et al.	437	182	03/14/1989	
Ah	US-4,931,410	06/05/1990	Tokunaga, Takafumi , et al.	437	189	08/25/1988

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*Anders Kuehl*

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete If Known

Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 2 of 13

Attorney Docket No: 303.686US3

<i>Qh</i>	US-4,948,459	08/14/1990	Van Laarhoven, , et al.	156	643	01/04/1989
	US-4,962,058	10/09/1990	Cronin, John E., et al.	437	187	04/14/1989
	US-4,996,584	02/26/1991	Young, P. L., et al.	357	71	10/13/1988
	US-5,019,531	05/28/1991	Awaya, N., et al.	437	180	05/19/1989
	US-5,034,799	07/23/1991	Tomita, K., et al.	357	71	02/14/1990
	US-5,045,635	09/02/1991	Kaplo, Joseph J., et al.	174	35 GC	06/16/1989
	US-5,084,412	01/28/1992	Nakasaka, Yasushi	437	189	10/01/1990
	US-5,100,499	03/31/1992	Douglas, M. A.	156	635	06/25/1991
	US-5,130,274	07/14/1992	Harper, J. M., et al.	437	195	04/05/1991
	US-5,148,260	09/15/1992	Inoue, T., et al.	357	67	09/07/1990
	US-5,149,615	09/22/1992	Chakravorty, K. K., et al.	430	313	01/08/1991
	US-5,158,986	10/27/1992	Cha, S. W., et al.	521	82	04/05/1991
	US-5,173,442	12/22/1992	Carey, D. H.	437	173	03/24/1992
	US-5,227,658	07/13/1993	Beyer, K., et al.	257	522	10/23/1991
	US-5,231,036	07/27/1993	Miyauchi, N., et al.			
	US-5,231,056	07/27/1993	Sandhu, G. S.	437	200	01/15/1992
	US-5,232,866	08/03/1993	Beyer, K., et al.	437	62	10/23/1991
	US-5,240,878	08/31/1993	Fitzsimmons, J., et al.	437	187	04/26/1991
	US-5,243,222	09/07/1993	Harper, J. M., et al.	257	774	01/08/1992
	US-5,256,205	10/26/1993	Schmitt III, Jerome J., et al.	118	723	01/07/1992
	US-5,268,315	12/07/1993	Prasad, J. S., et al.	437	31	09/04/1992
	US-5,308,440	05/03/1994	Chino, T., et al.	156	664	09/02/1992
	US-5,324,683	06/28/1994	Fitch, J. T., et al.	437	65	06/02/1993
	US-5,324,684	06/28/1994	Kermani, Ahmad, et al.	437	95	02/25/1992
	US-5,334,356	08/02/1994	Baldwin, D. F., et al.	422	133	08/24/1992
	US-5,336,914	08/09/1994	Andoh, Takeshi	257	368	06/19/1992
	US-5,354,712	10/11/1994	Ho, Y. Q., et al.	437	195	11/12/1992
	US-5,356,672	10/18/1994	Schmitt III, J. J., et al.	427	446	05/09/1990
	US-5,371,042	12/06/1994	Ong, E.	437	194	06/16/1992
	US-5,384,284	01/24/1995	Doan, T. T., et al.	437	190	10/01/1993
	US-5,399,897	03/21/1995	Cunningham, B. T., et al.	257	467	11/29/1993
	US-5,408,742	04/25/1995	Zaidel, S. A., et al.	29	846	10/22/1993
	US-5,413,687	05/09/1995	Barton, C. L., et al.	204	192.14	11/27/1991
	US-5,413,962	05/09/1995	Lur, Water, et al.	437	195	07/15/1994
<i>Qh</i>	US-5,424,030	06/13/1995	Takahashi, H.	420	473	12/03/1993
	US-5,426,330	06/20/1995	Joshi, R. V., et al.	257	752	09/21/1993

EXAMINER

*Adh. H. H. H. H.*

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*10/28/95*

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in compliance with MPEP 809. Draw line through citation if not in compliance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)	Complete If Known	
	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 3 of 13		Attorney Docket No: 303.686US3

Ah	US-5,442,237	08/15/1995	Hughes, Henry G., et al.	257	759	02/04/1994
	US-5,444,015	08/22/1995	Aitken, John M., et al.	437	182	04/11/1994
	US-5,447,887	09/05/1995	Filipiak, Stanley, et al.	437	200	04/01/1994
	US-5,457,344	10/10/1995	Bartelink, Dirk J.	257	737	03/25/1994
	US-5,470,789	11/28/1995	Misawa, N.	437	190	03/07/1995
	US-5,470,801	11/28/1995	Kapoor, Ashok K., et al.	437	238	06/28/1993
	US-5,476,817	12/19/1995	Numata, K.	437	195	05/31/1994
	US-5,485,037	01/16/1996	Marrs, R. C.	257	712	03/27/1995
	US-5,495,667	03/05/1996	Farnworth, Warren M., et al.	29	843	11/07/1994
	US-5,506,449	04/09/1996	Nakano, Tadashi, et al.	257	758	03/23/1994
	US-5,510,645	04/23/1996	Fitch, J. T., et al.	257	522	01/17/1995
	US-5,529,956	06/25/1996	Morishita, Y.	437	195	09/28/1994
	US-5,534,731	07/09/1996	Cheung, Robin	257	759	10/28/1994
	US-5,538,922	07/23/1996	Cooper, K J., et al.	437	195	01/25/1995
	US-5,539,060	07/23/1996	Tsunogae, Y., et al.	525	338	10/13/1995
	US-5,539,227	07/23/1996	Nakano, H.	257	276	08/02/1995
	US-5,578,146	11/26/1996	Grant, L. A., et al.	148	437	01/16/1996
	US-5,595,937	01/21/1997	Mikagi, K.	437	192	04/12/1996
	US-5,609,721	03/11/1997	Tsukune, A, et al.	156	646.1	01/03/1995
	US-5,625,232	04/29/1997	Numata, K., et al.	257	758	07/15/1994
	US-5,635,253	06/03/1997	Canaperi, Donald F., et al.	427	437	06/07/1995
	US-5,654,245	08/05/1997	Allen, Gregory L.	438	629	03/23/1993
	US-5,662,788	09/02/1997	Sandhu, G., et al.	205	87	06/03/1996
	US-5,667,600	09/16/1997	Grensing, Fritz C., et al.	148	437	03/31/1994
	US-5,670,420	09/23/1997	Choi, Kyeong K.	437	189	11/08/1995
	US-5,674,787	10/07/1997	Zhao, Bin, et al.	437	230	01/16/1996
	US-5,675,187	10/07/1997	Numata, K., et al.	257	758	05/16/1996
	US-5,679,608	10/21/1997	Cheung, Robin W., et al.	437	195	06/05/1995
	US-5,681,441	10/28/1997	Svensen, Leo G., et al.	205	114	12/22/1992
	US-5,695,810	12/09/1997	Dubin, Valery M., et al.	427	96	11/20/1996
	US-5,705,425	01/06/1998	Miura, T., et al.	437	182	04/26/1996
	US-5,719,089	02/17/1998	Cherng, Meng-Jaw, et al.	438	637	06/21/1996
Ah	US-5,719,410	02/17/1998	Suehiro, S., et al.	257	77	12/16/1996

EXAMINER

*Andy Murray*

DATE CONSIDERED

10/08/04

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)	<i>Complete if Known</i>	
	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 4 of 13	Attorney Docket No: 303.686US3	

OK	US-5,725,689	03/10/1998	Nishida, S. , et al.	148	320	10/05/1995
	US-5,739,579	04/14/1998	Chiang, Chien , et al.	257	635	09/10/1996
	US-5,763,953	06/09/1998	Iijima, T. , et al.	257	762	01/18/1996
	US-5,780,358	07/14/1998	Zhou, M. S.	438	645	04/08/1996
	US-5,785,570	07/28/1998	Bruni, M. D.	445	52	07/25/1995
	US-5,792,522	08/11/1998	Jin, S. , et al.	427	575	09/18/1996
	US-5,792,706	08/11/1998	Michael, M. W., et al.	438	626	06/05/1996
	US-5,801,098	09/01/1998	Fiordalice, R. , et al.	438	653	09/03/1996
	US-5,814,557	09/29/1998	Venkatraman, Ramnath , et al.	438	622	05/20/1996
	US-5,821,168	10/13/1998	Jain, Ajay	438	692	07/16/1997
	US-5,824,599	10/20/1998	Schacham-Diamond, Yosef , et al.	438	678	01/16/1996
	US-5,852,871	12/29/1998	Khandros, I. Y.	29	843	12/11/1995
	US-5,858,877	01/12/1999	Dennison, C. H., et al.	438	700	01/21/1997
	US-5,880,018	03/01/1999	Boeck, Bruce A., et al.	438	619	
✓	US-5,891,797	04/06/1999	Farrar, P. A.	438	619	10/20/1997
	US-5,891,804	04/06/1999	Havemann, R. H., et al.	438	674	04/14/1997
	US-5,893,752	04/13/1999	Zhang, J. , et al.	438	687	12/22/1997
	US-5,895,740	04/20/1999	Chien, Rong-Wu , et al.	430	313	11/13/1996
	US-5,897,370	04/27/1999	Joshi, R. V., et al.	438	632	10/28/1996
	US-5,900,668	05/04/1999	Wollesen, D. L.	257	522	11/30/1995
	US-5,907,772	05/25/1999	Iwasaki, Haruo	438	253	02/26/1997
	US-5,911,113	06/08/1999	Yao, G. , et al.	438	649	03/18/1997
	US-5,913,147	06/15/1999	Dubin, Valery , et al.	438	687	01/21/1997
	US-5,925,930	07/20/1999	Farnworth, Warren M., et al.	257	737	05/21/1996
	US-5,930,596	07/27/1999	Klose, H. , et al.	438	98	03/07/1995
	US-5,930,669	07/27/1999	Uzoh, Cyprian	438	627	04/03/1997
	US-5,932,928	08/03/1999	Clampitt, D. A.	257	758	07/03/1997
	US-5,933,758	08/03/1999	Jain, A.	438	687	05/12/1997
	US-5,940,733	08/17/1999	Beinglass, Israel , et al.	438	655	07/29/1997
	US-5,948,467	09/07/1999	Nguyen, T. , et al.	427	99	07/24/1998
	US-5,962,923	10/05/1999	Xu, Z. , et al.	257	774	08/07/1995
	US-5,968,333	10/19/1999	Nogami, T. , et al.	205	184	04/07/1998
	US-5,969,422	10/19/1999	Ting, C. , et al.	257	762	05/15/1997
	US-5,972,179	10/26/1999	Chittipeddi, , et al.	204	192.17	09/30/1997
	US-5,972,804	10/26/1999	Tobin, Philip J., et al.	438	786	11/03/1997
OK	US-5,976,710	11/02/1999	Sachdev, K. G., et al.	428	620	04/10/1997

EXAMINER

*Andrew H. [Signature]*

DATE CONSIDERED

10/08/02

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	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 5 of 13		Attorney Docket No: 303.686US3

ah	US-5,981,350	11/09/1999	Geusic, Joseph E., et al.	438	386	05/29/1998
	US-5,985,759	11/16/1999	Kim, E., et al.	438	653	02/24/1998
	US-5,989,623	11/23/1999	Chen, Liang-Yuh, et al.	427	97	08/19/1997
	US-5,994,776	11/30/1999	Fang, Peng, et al.	257	758	04/20/1998
	US-5,994,777	11/30/1999	Farrar, P. A.	257	758	08/26/1998
	US-6,001,730	12/14/1999	Farkas, J., et al.	438	627	10/20/1997
	US-6,004,884	12/21/1999	Abraham, L. C.	438	714	02/15/1996
	US-6,008,117	12/28/1999	Hong, Qi-Zhong, et al.	438	629	03/19/1997
	US-6,015,465	01/18/2000	Kholodenko, A., et al.	118	719	04/08/1998
	US-6,015,738	01/18/2000	Levy, H. J., et al.	438	275	11/17/1997
	US-6,017,820	01/25/2000	Ting, C. H., et al.	438	689	07/17/1998
	US-6,022,802	02/08/2000	Jang, Syun-Ming	438	656	03/18/1999
	US-6,025,261	02/15/2000	Farrar, C., et al.	438	619	04/29/1998
	US-6,030,877	02/29/2000	Lee, C., et al.	438	381	10/06/1997
	US-6,037,248	03/14/2000	Ahn, Kie	438	619	06/13/1997
	US-6,054,172	04/25/2000	Robinson, K., et al.	427	97	02/25/1999
	US-6,057,226	05/02/2000	Wong, L. D.	438	623	11/25/1997
	US-6,065,424	05/23/2000	Shacham-Diamand, Y., et al.	118	696	12/18/1996
	US-6,069,068	05/30/2000	Rathore, H. S., et al.	438	628	10/08/1997
	US-6,071,810	06/06/2000	Wada, Junichi, et al.	438	635	12/23/1997
	US-6,075,278	06/13/2000	Farrar, P. A.	257	522	04/24/1997
	US-6,075,287	06/13/2000	Ingraham, A. P., et al.			
	US-6,091,136	07/18/2000	Jiang, T., et al.	257	676	11/17/1998
	US-6,091,475	07/18/2000	Ogino, T., et al.	349	149	12/09/1997
	US-6,100,193	08/08/2000	Suehiro, S., et al.	438	685	09/24/1997
	US-6,121,126	09/19/2000	Ahn, Kie, et al.	438	602	02/25/1998
	US-6,126,989	10/03/2000	Robinson, Karl, et al.	427	97	08/26/1998
	US-6,136,095	10/24/2000	Xu, Z., et al.	118	719	10/06/1997
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Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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Examiner Name	Unknown

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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
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